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Cont. waveguide layer, in the transverse direction. After the inorganic protective layers 8 are subjected to etching until the surface of the grating layer 7a is exposed, the resist mask 13 is removed to thereby form the through grooves on the inorganic protective layers 8.

IN THE CLAIMS:

Please enter the following amended claims:

Sub B7
Q2 1. (Amended) A DFB type semiconductor laser device comprising a laser substrate, a grating layer, an insulating layer and an electrode layer laminated in order, the insulating layer including at least one gap extending in a direction transverse to a grating of the grating layer so that the electrode layer contacts the grating layer and a clad layer.

A3 Sub C17
3. (Amended) The DFB type semiconductor laser device according to claim 2, wherein the clad layer has a thickness equal to or thinner than 0.5 μm .

IN THE ABSTRACT:

Please delete the Abstract of the Disclosure and insert therefor the following
Abstract of the Disclosure:

A4 A DFB type semiconductor laser device including a laser substrate, a grating layer, an insulating layer and an electrode layer, which are laminated in the given order. The insulating layer includes a through groove or grooves extending to the grating layer in a direction in which a resonator of the laser device is formed, and the electrode layer contacts the grating layer and a clad layer.